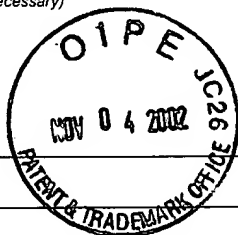


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Sheet 1 of 2

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Application Number	09/135413
Filing Date	August 14, 1998
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Nguyen, Viet
Attorney Docket No:	00303.354US2

Viet Q. Nguyen  
Primary Examiner

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Primary Examiner

**FOREIGN PATENT DOCUMENTS**

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Primary Examiner

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
W		BELTRAM, F., et al. "GaAlAs/GaAs Floating-Gate Memory Devices with Graded-Gap Injector Grown by Molecular-Beam Epitaxy", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-7, (Dec. 1988), 2451	
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V. Nguyen

DATE CONSIDERED

12/28/02

Substitute Disclosure Statement Form (PTO-1449)

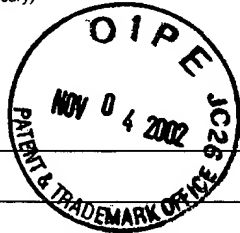
\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Sheet 2 of 2

Attorney Docket No: 00303.354US2

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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